

60 V, 6 A NPN low V_{CEsat} (BISS) transistor Rev. 1 — 19 May 2010

Product data sheet

1. **Product profile**

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5560PA.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	6	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-	7	A
R _{CEsat}	collector-emitter saturation resistance	I _C = 6 A; I _B = 300 mA	<u>[1]</u> -	34	48	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



60 V, 6 A NPN low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector		1-2
		1 2	sym021
		Transparent top view	

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PBSS4560PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061	

4. Marking

Table 4.	Marking codes	
Type num	iber	Marking code
PBSS456	0PA	A8

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	-		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	60	V
V _{CEO}	collector-emitter voltage	open base	-	60	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	6	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	7	А
I _B	base current		-	600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	500	mW
			[2] _	1	W
			<u>[3]</u> _	1.4	W
			[4] _	2.1	W

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

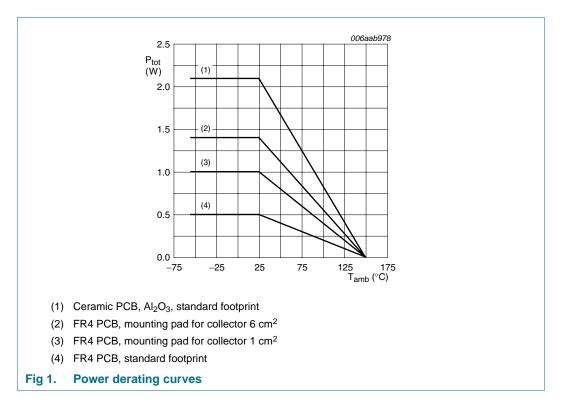
Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	-	250	K/W
	junction to ambient		[2] _	-	125	K/W
			[3]	-	90	K/W
			[4]	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

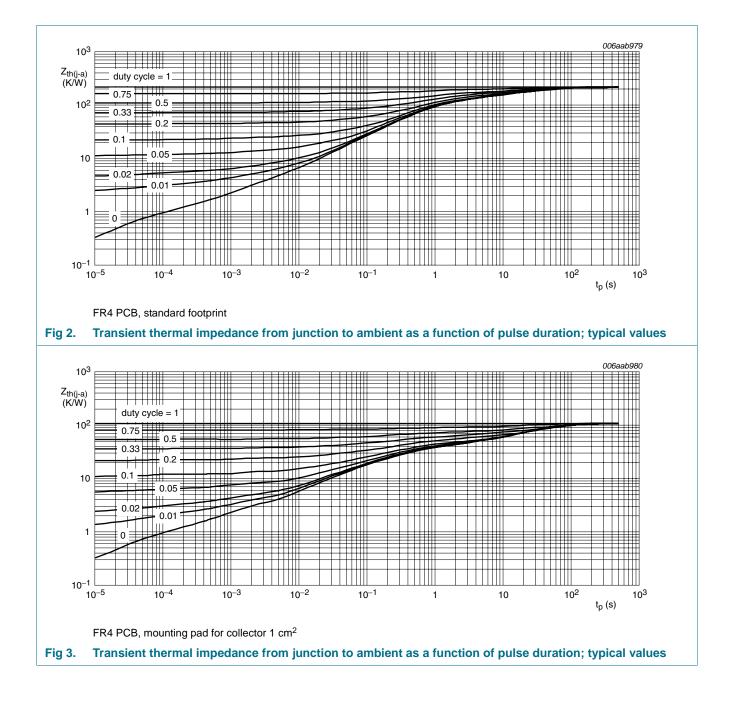
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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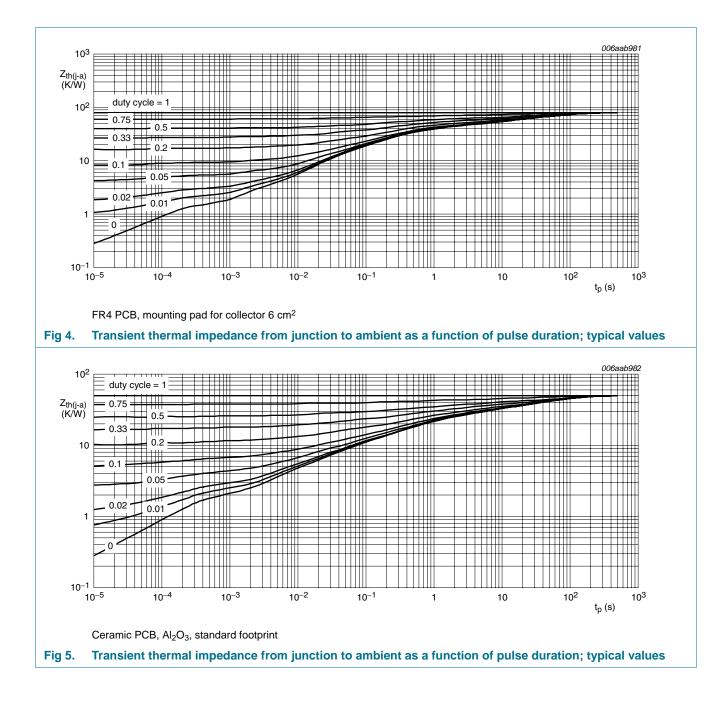
60 V, 6 A NPN low V_{CEsat} (BISS) transistor



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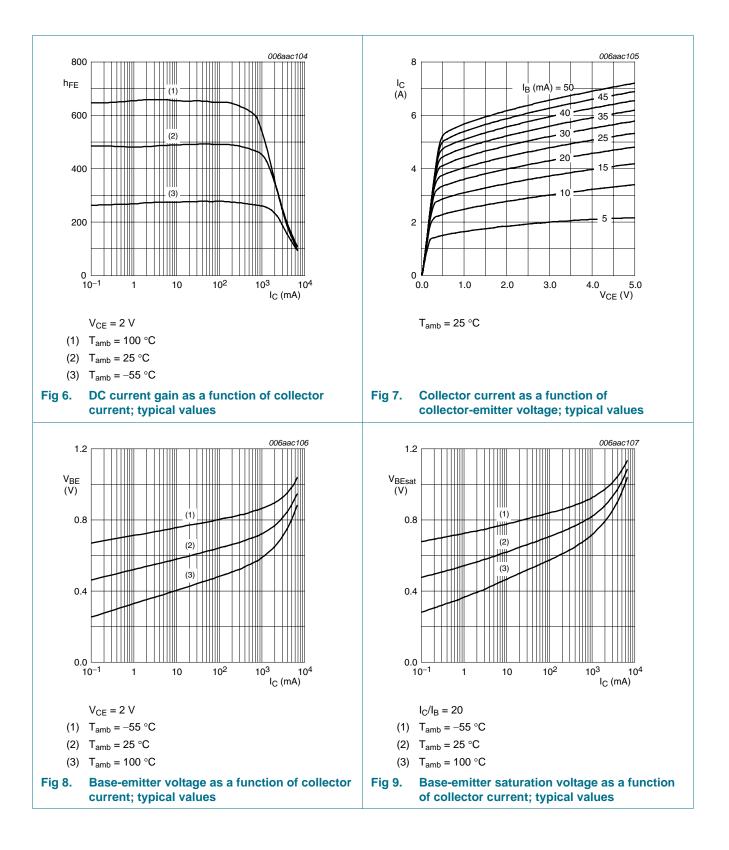
60 V, 6 A NPN low V_{CEsat} (BISS) transistor

7. Characteristics

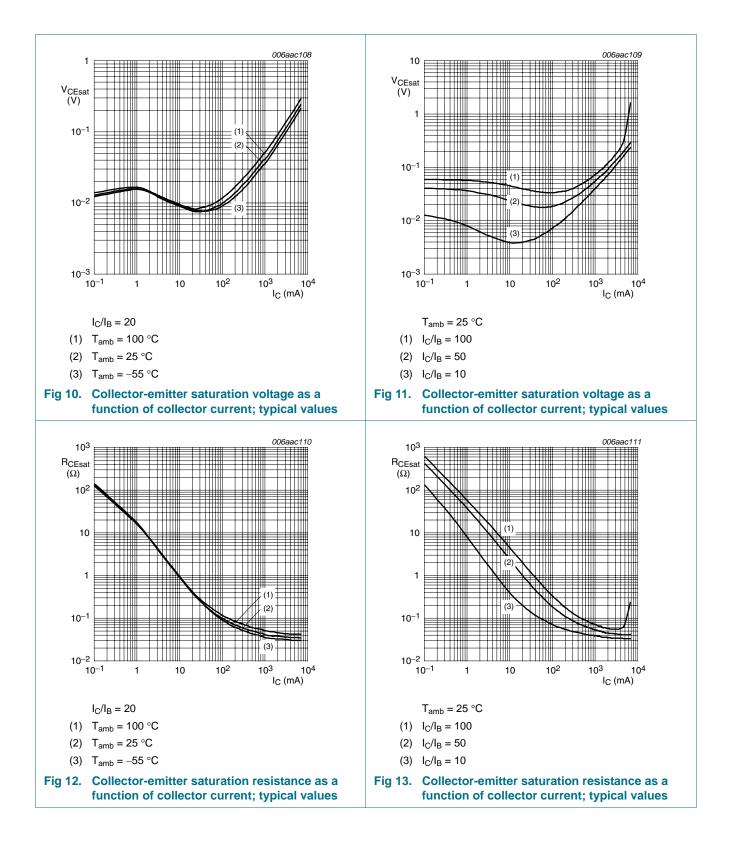
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base	$V_{CB} = 48 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	cut-off current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = 48 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 V$	<u>[1]</u>			
		I _C = 0.5 A	280	440	-	
		I _C = 1 A	260	420	-	
		I _C = 2 A	210	325	-	
		I _C = 6 A	70	120	-	
V _{CEsat} collecto	collector-emitter	$I_{C} = 0.5 \text{ A}; I_{B} = 50 \text{ mA}$	<u>[1]</u> -	22	30	mV
	saturation voltage	$I_{C} = 1 \text{ A}; I_{B} = 50 \text{ mA}$	<u>[1]</u> -	45	60	mV
		$I_{C} = 1 \text{ A}; I_{B} = 10 \text{ mA}$	<u>[1]</u> -	70	95	mV
		$I_{C} = 2 \text{ A}; I_{B} = 20 \text{ mA}$	<u>[1]</u> -	115	170	mV
		$I_{C} = 3 \text{ A}; I_{B} = 30 \text{ mA}$	<u>[1]</u> -	165	250	mV
		$I_{C} = 4 \text{ A}; I_{B} = 400 \text{ mA}$	<u>[1]</u> -	130	200	mV
		$I_{C} = 6 \text{ A}; I_{B} = 300 \text{ mA}$	<u>[1]</u> -	200	290	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = 6 A; I _B = 300 mA	<u>[1]</u> -	34	48	mΩ
V _{BEsat}	base-emitter	I _C = 1 A; I _B = 10 mA	<u>[1]</u> -	0.75	0.9	V
	saturation voltage	$I_{C} = 6 \text{ A}; I_{B} = 300 \text{ mA}$	<u>[1]</u> -	0.97	1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 2 \text{ A}$	<u>[1]</u> -	0.75	0.9	V
t _d	delay time	$V_{CC} = 9 V; I_C = 2 A;$	-	22	-	ns
t _r	rise time	I _{Bon} = 0.1 A; I _{Boff} = -0.1 A	-	101	-	ns
t _{on}	turn-on time	BOll0.1 V	-	123	-	ns
t _s	storage time		-	635	-	ns
t _f	fall time		-	145	-	ns
t _{off}	turn-off time		-	780	-	ns
f⊤	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz	90	150	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	23	30	pF

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60 V, 6 A NPN low V_{CEsat} (BISS) transistor

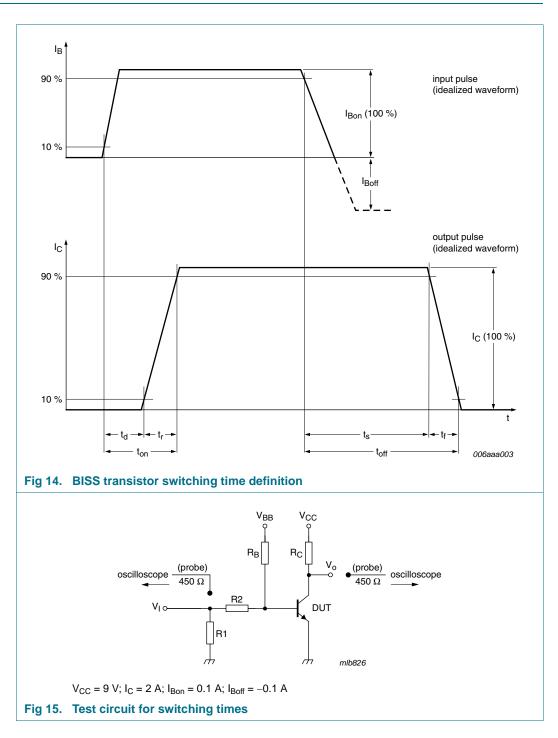


60 V, 6 A NPN low V_{CEsat} (BISS) transistor



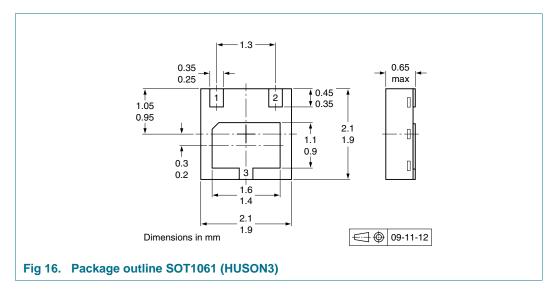
60 V, 6 A NPN low V_{CEsat} (BISS) transistor

8. Test information



60 V, 6 A NPN low V_{CEsat} (BISS) transistor

9. Package outline



10. Packing information

Table 8. Packing methods

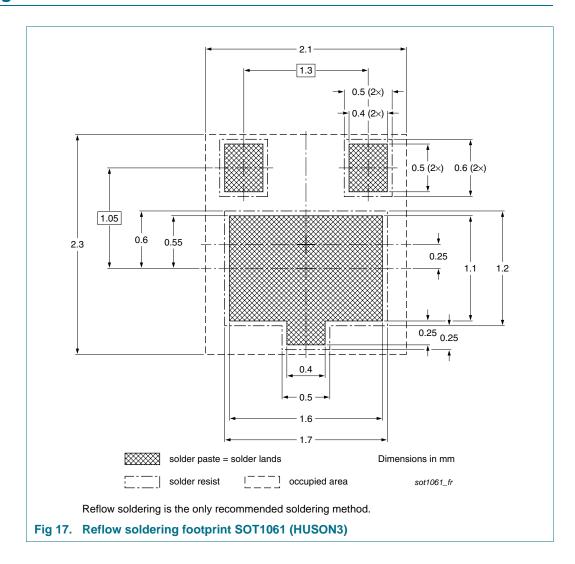
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS4560PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

11. Soldering



Product data sheet

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision hist	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4560PA v.1	20100519	Product data sheet	-	-	

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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PBSS4560PA

13 of 15

60 V, 6 A NPN low V_{CEsat} (BISS) transistor

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60 V, 6 A NPN low V_{CEsat} (BISS) transistor

15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 3
7	Characteristics
8	Test information 9
9	Package outline 10
10	Packing information 10
11	Soldering 11
12	Revision history 12
13	Legal information 13
13.1	Data sheet status 13
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 14
14	Contact information 14
15	Contents 15

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